Unit: mm

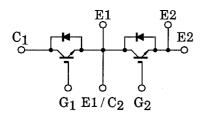
TOSHIBA GTR Module Silicon N Channel IGBT

MG30V2YS40

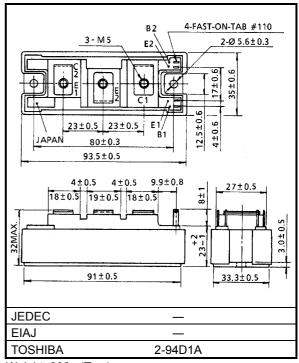
High Power Switching Applications Motor Control Applications

- The electrodes are isolated from case.
- High input impedance
- Includes a complete half bridge in one package.
- Enhancement-mode
- High speed : $t_f = 1.5 \mu s$ (Max.) (IC = 30A) $t_{rr} = 0.3 \mu s$ (Max.) (IF = 30A)

Equivalent Circuit



Maximum Ratings (Ta = 25°C)



Weight: 202g (Typ.)

Characteris	Symbol	Rating	Unit		
Collector-emitter voltage		V _{CES}	1700	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	Ι _C	30	^	
	1ms	I _{CP}	60	A	
Forward current	DC	١ _F	30	A	
	1ms	I _{FM}	60		
Collector power dissipation (Tc = 25°C)		PC	500	W	
Junction temperature		Тj	150	°C	
Storage temperature range		T _{stg}	-40 ~ 125	°C	
Isolation voltage		V _{Isol}	4000 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		—	3/3	N∙m	

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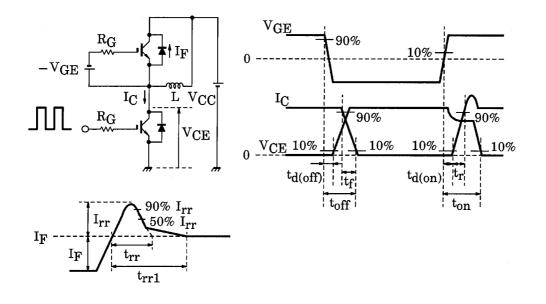
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Electrical Characteristics (Ta = 25°C)

Cł	naracteristic	Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V_{GE} = ±20V, V_{CE} = 0		_	_	±50	nA
Collector cut-off current		ICES	V _{CE} = 1700V, V _{GE} = 0			_	0.5	mA
Gate-emitter cut-off voltage		V _{GE (off)}	I _C = 30mA, V _{CE} = 5V		4.0	_	8.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 30A, V _{GE} = 15V		_	3.2	4.5	V
Input capacitance		C _{ies}	V _{CE} = 10V, V _{GE} = 0, f = 1MHz		_	4400	_	pF
Switching time	Turn-on delay time	t _{d (on)}			_	0.1		-
	Rise time	t _r	Inductive load $V_{CC} = 900V$ $I_C = 30A$ $V_{GE} = \pm 15V$ $R_G = 24\Omega$		_	0.1		
	Turn-on time	t _{on}			_	0.5		
	Turn-off delay time	t _{d (off)}		(Note 1)	_	0.4		- µs
	Fall time	t _f			_	0.5	1.5	
	Turn-off time	t _{off}				1.0		
Forward voltage		V _F	I _F = 30 A, V _{GE} = 0			3.2	4.5	V
Reverse recovery time		t _{rr}	$I_F = 30 \text{ A}, V_{GE} = -15 \text{ V},$ di / dt = 500 A / μ s ((Note 1)	_	0.1	0.3	μs
Thermal resistance		R _{th (j-c)}	Transistor stage		_	—	0.25	°C/W
			Diode stage		_	—	1.0	

Note 1: Switching time and reverse recovery time test circuit & timing chart

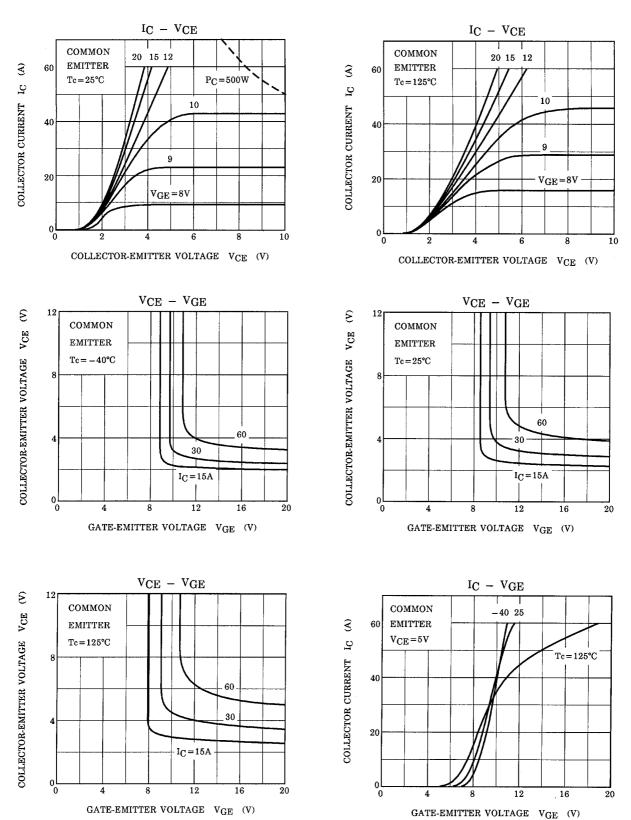


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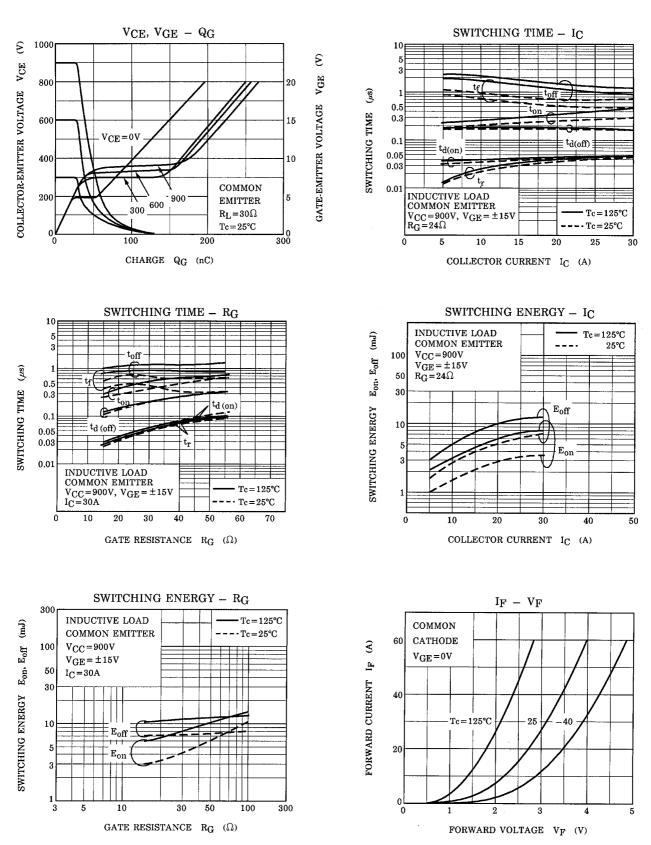
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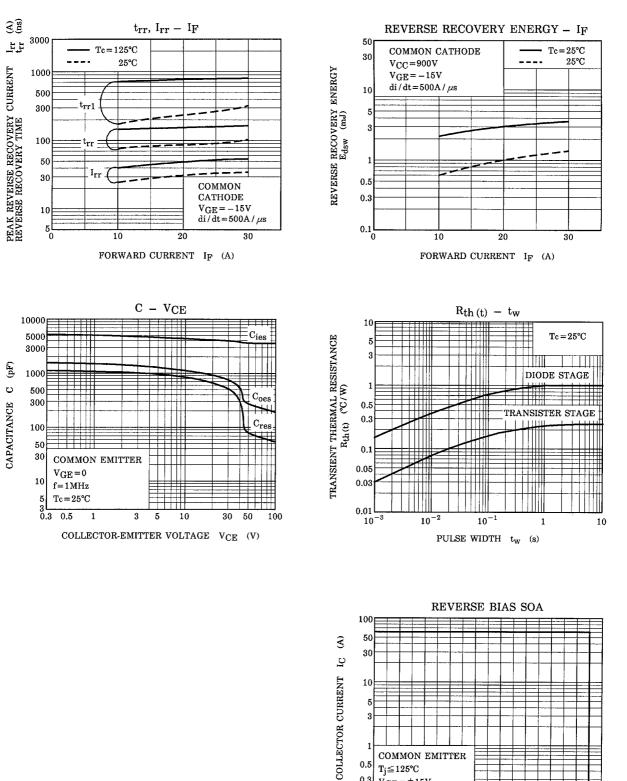
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0.3

0.1L 0

 $V_{GE} = \pm 15V$ $R_G = 24\Omega$

> 200 400 600 800 1000 1200 1400 1600 1800 Collector-emitter voltage v_{CE} (V)